
Electromagnetic Field Visualization System for IC/Package Design Based on Optical Techniques

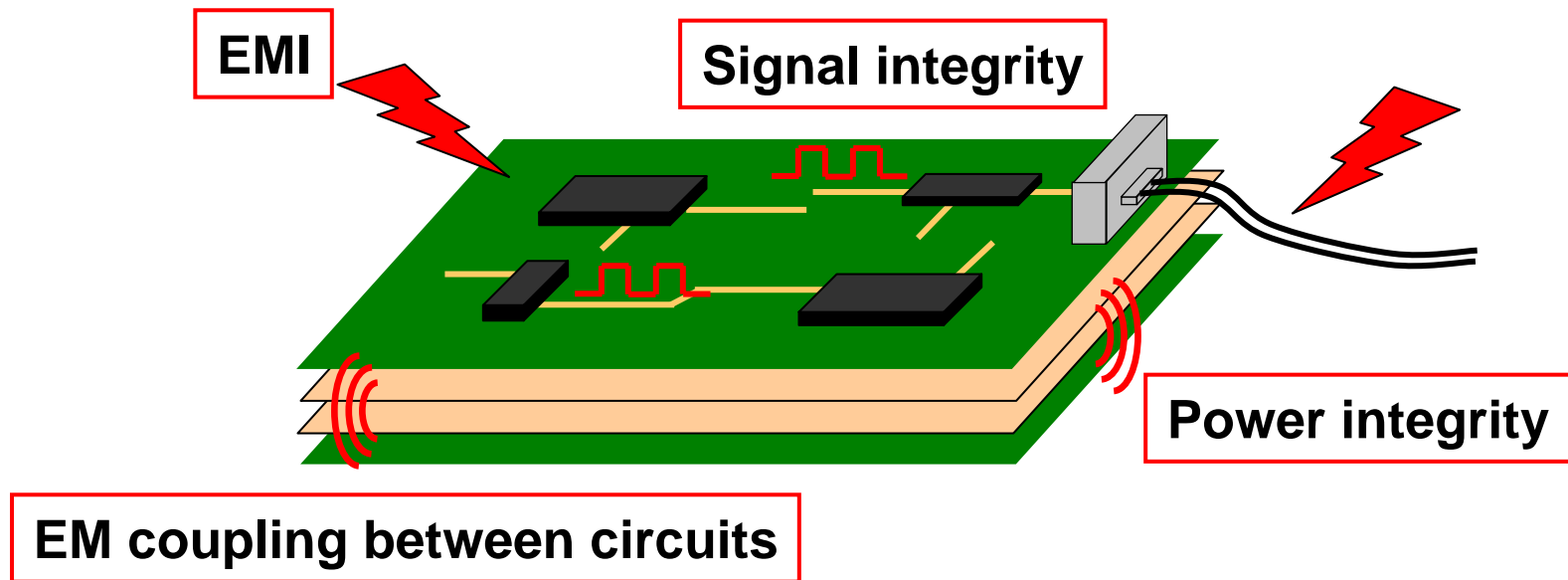
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Contents

- 1. Background and motivation**
- 2. Probing system: Fiber-Edge Magneto-Optic/Electro-Optic (FEMO/EO) Probe**
- 3. Objective**
- 4. Magnetic near-field maps over fine meander circuits**
 - 4-1. Probe head and device under test**
 - 4-2. Mapping results**
 - 4-3. Verification of measured results by electromagnetic field simulator**
- 5. Electromagnetic near-field measurements over active devices**
 - 5-1. Measurement results of radiated emissions and near-fields arising from a PCB**
 - 5-2. Magnetic/electric near-field maps over an LSI chip**
- 6. Conclusions**

Background and motivation

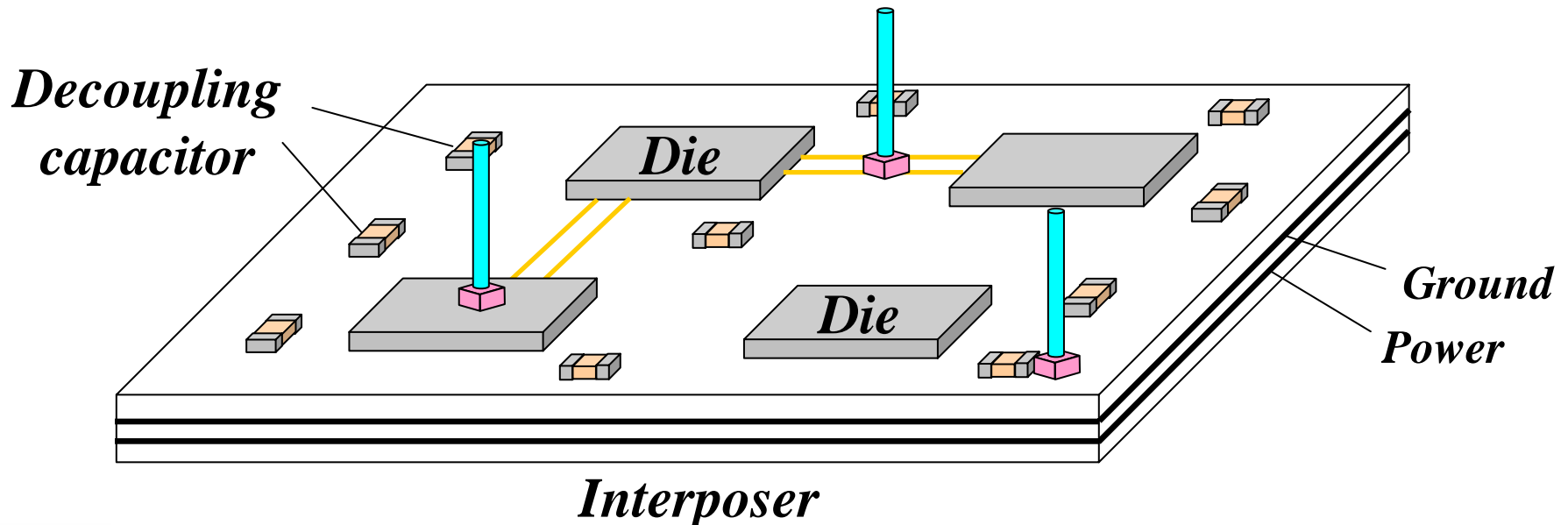
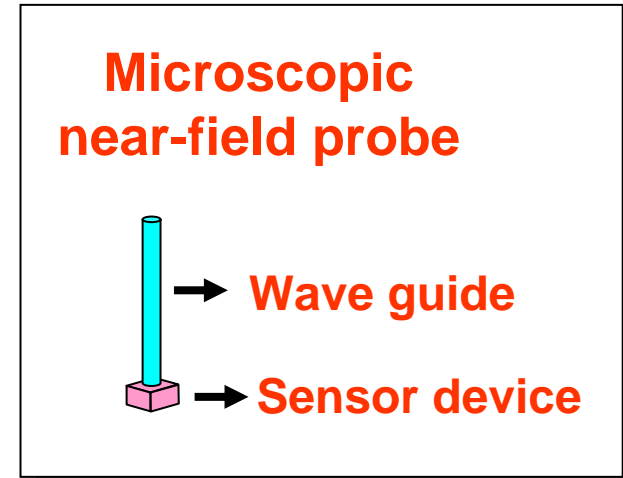


It is highly desirable to prevent the problems in the early stages of design and packaging of electronic components.

Background and motivation

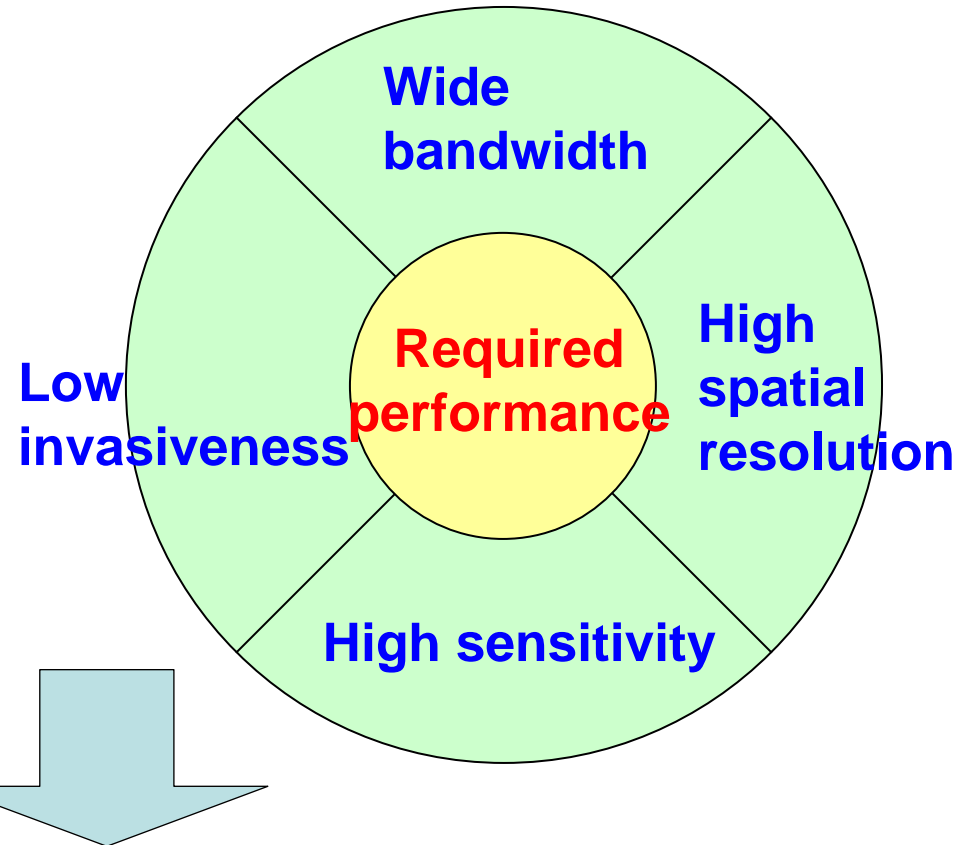
Conventional circuit performance evaluation/testing techniques such as a network analyzer and a TDR

It is difficult to identify the concrete location of the faulty components inside the circuits. They cannot give direct information about an EM coupling position and individual decoupling capacitor performance.



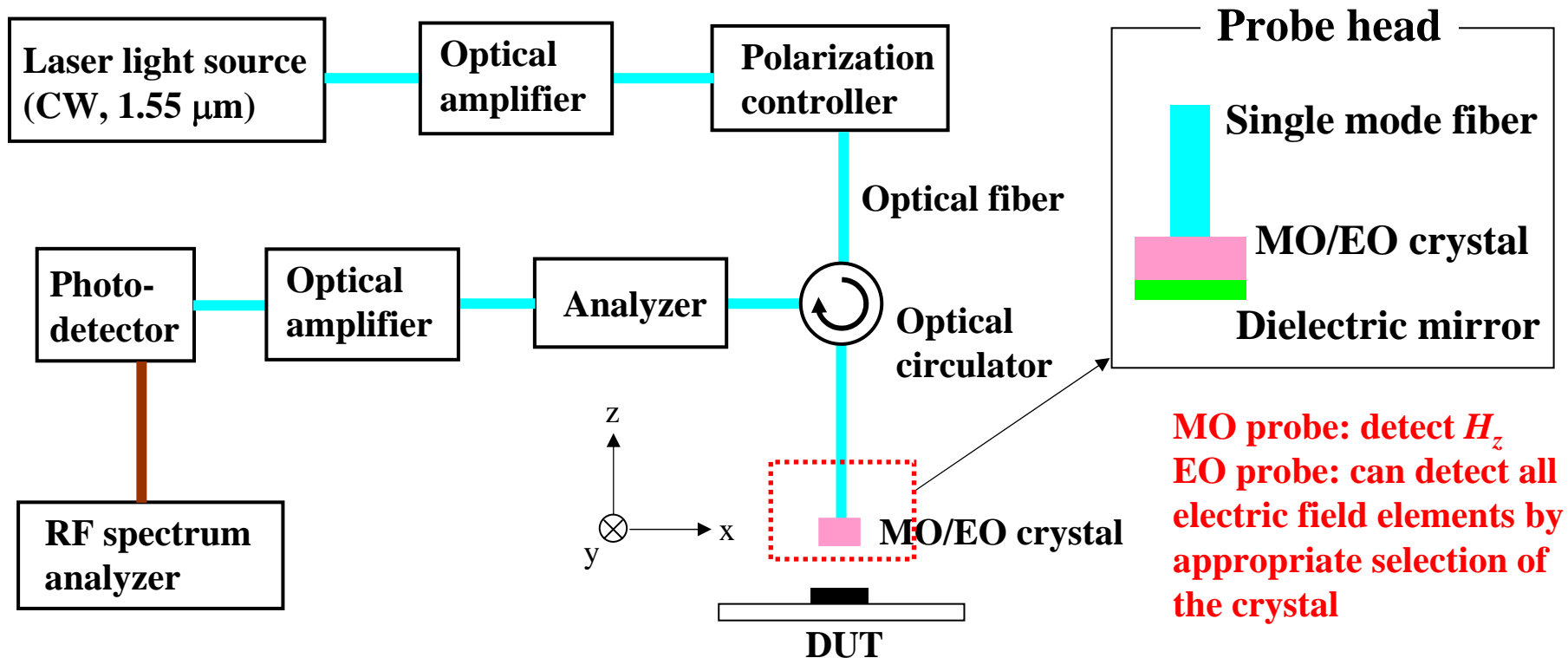
Background and motivation

Near-field probing technique is one of indispensable techniques.



Development and evaluations of a near-field probe that utilizes optical measurement techniques.

FEMO/EO probing system



All apparatuses in the optical system are connected by optical fibers.

Free from optical alignment

The probe head consists of an optical fiber and a minute crystal.

Superior low-invasiveness

High spatial resolution

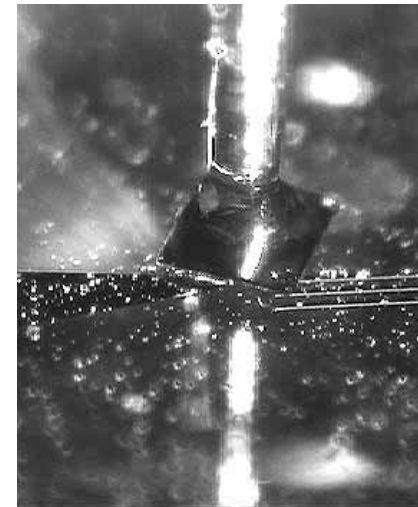
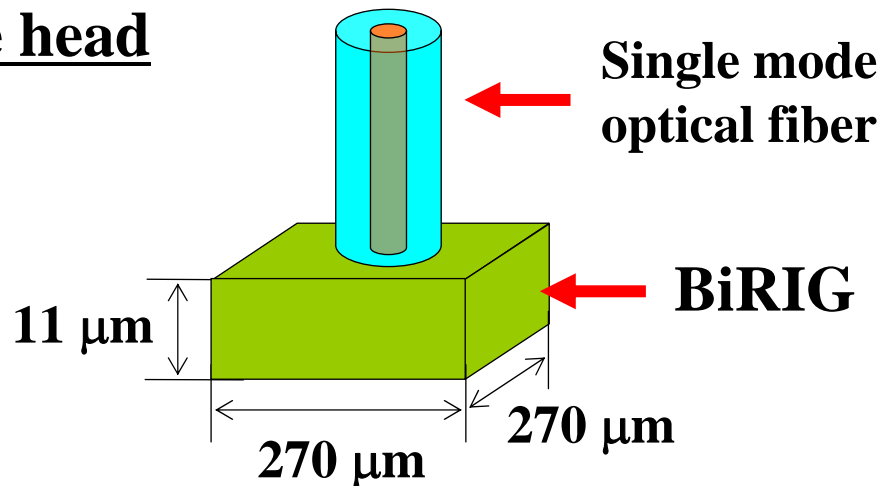
Objective

Development and application of high performance near-field probing system toward the high-speed and low-noise design of ICs/packages.

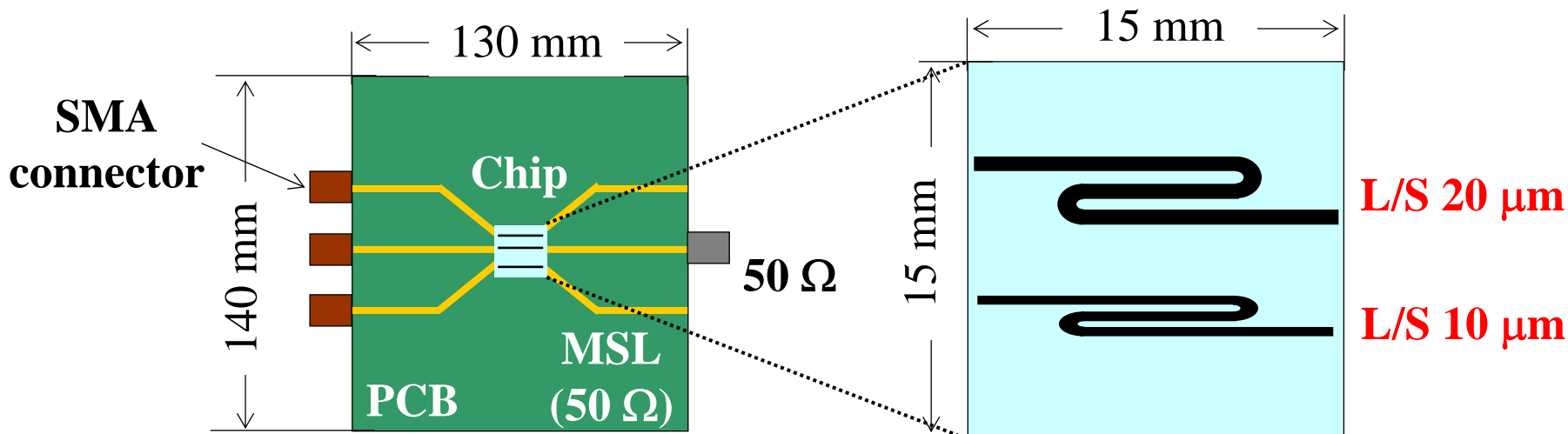
Magnetic near-field maps over fine meander circuits

Probe head and device under test (DUT)

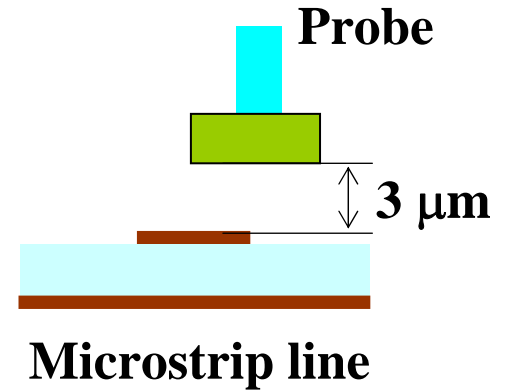
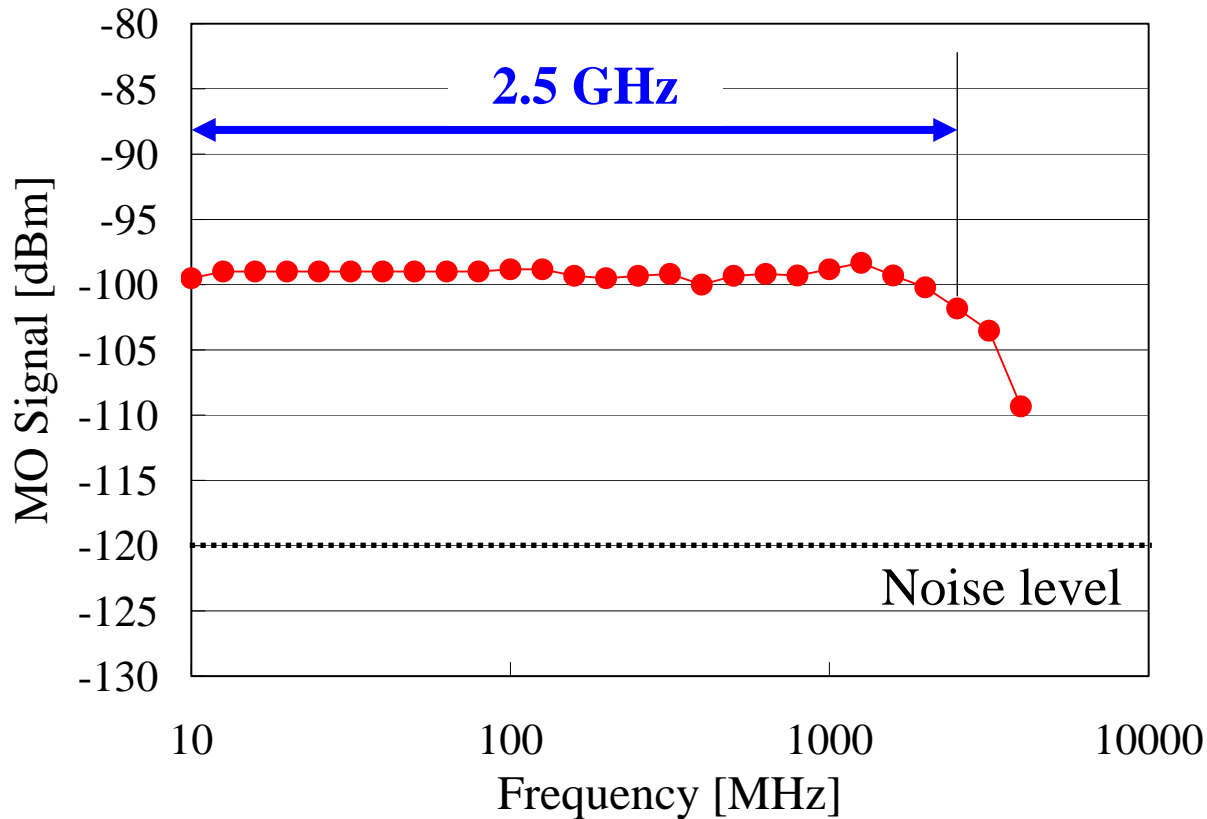
Probe head



DUT for near-field mappings



Frequency response of the FEMO probe



The range where the signal level undulation stays within 3 dB.

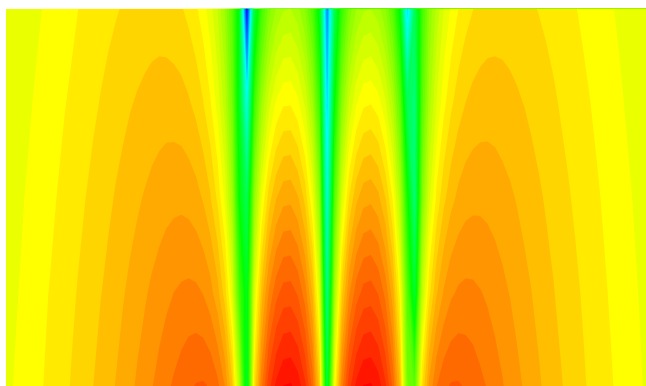


2.5 GHz

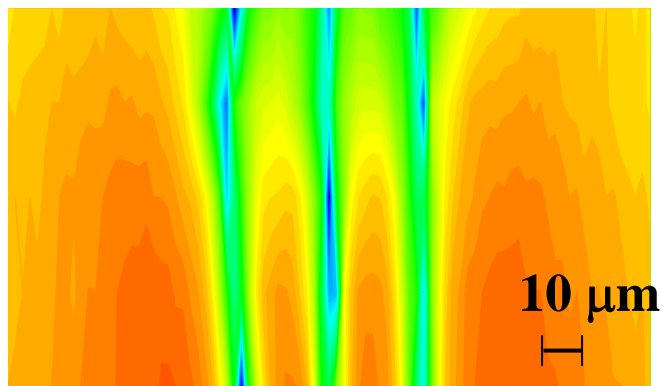
X-Z near-field maps

10 MHz

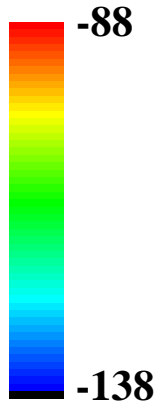
Cal.



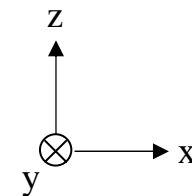
Exp.



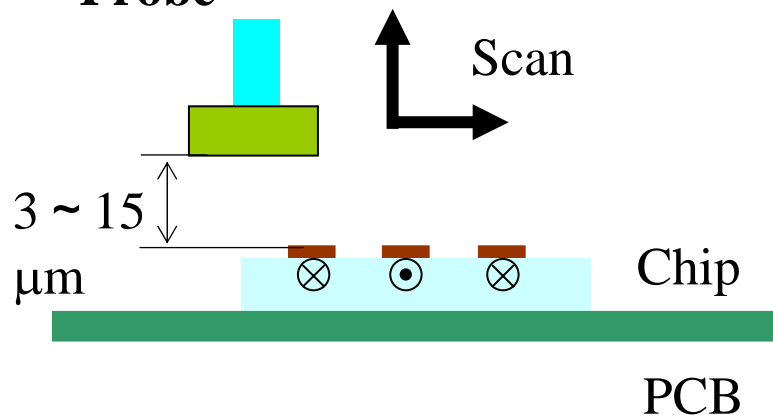
[dBm]



DUT



Probe

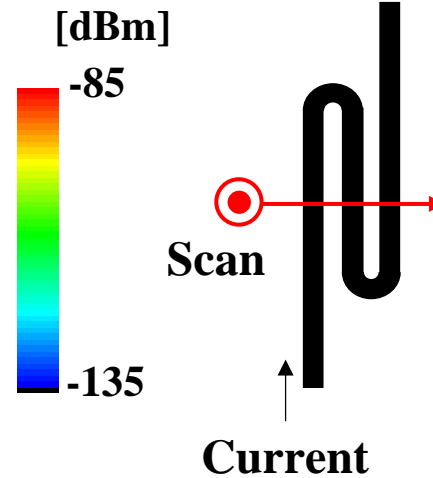
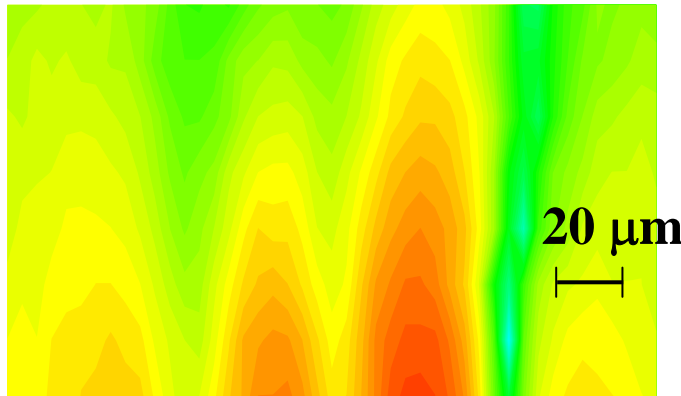


Line/Space 10 μm

X-Z near-field map

1 GHz

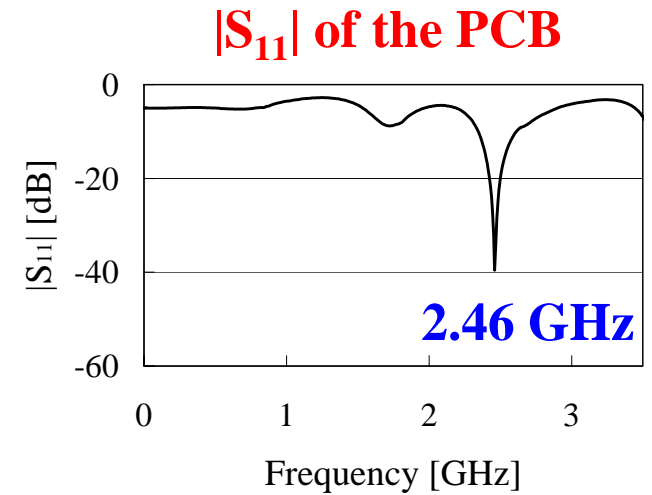
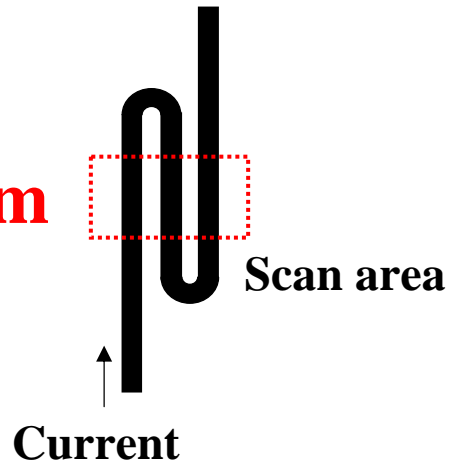
Exp.



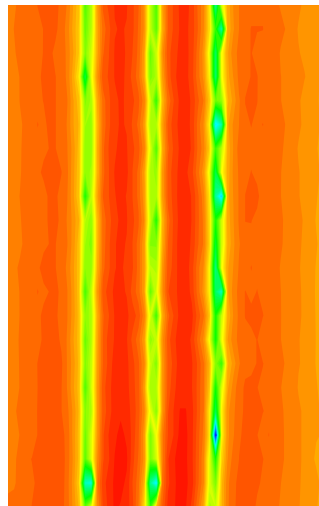
Line/Space 20 μm

X-Y near-field maps

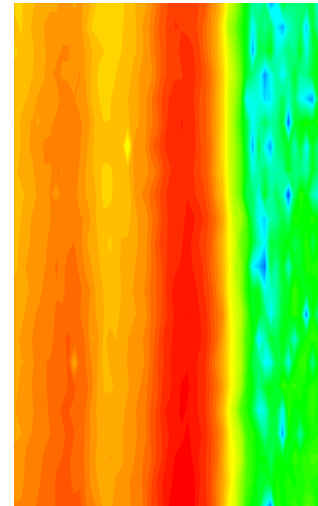
Line/Space $20\ \mu\text{m}$



10 MHz



2.46 GHz



50 μm

Verification of measured results by electromagnetic field simulator

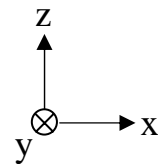
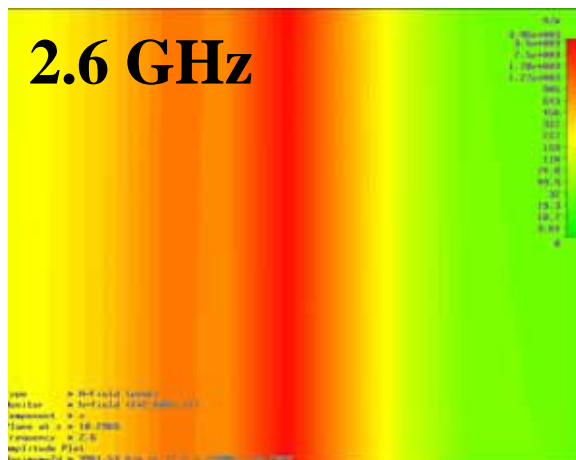
Simulated maps of the amplitude of H_z at nearby the middle position of the circuit.

X-Z map



These results suggest that the measured near-field maps are accurate.

X-Y map



Line/Space 20 μm
meander circuit

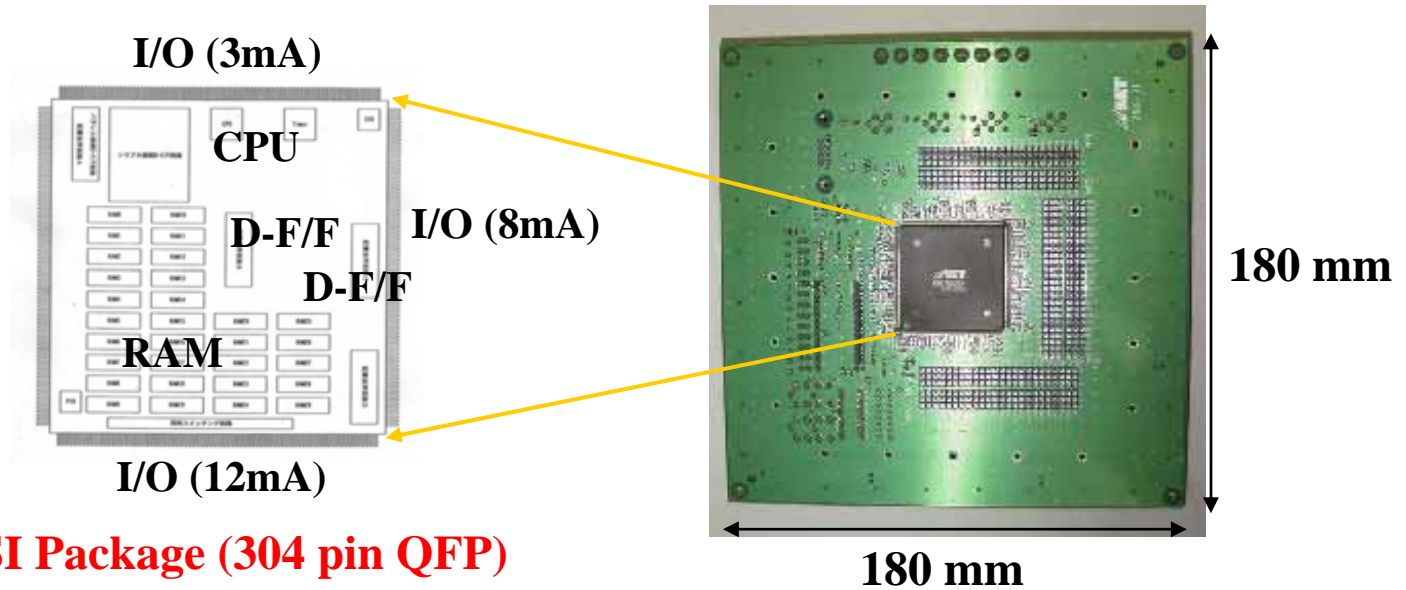
dielectric

Ground plane

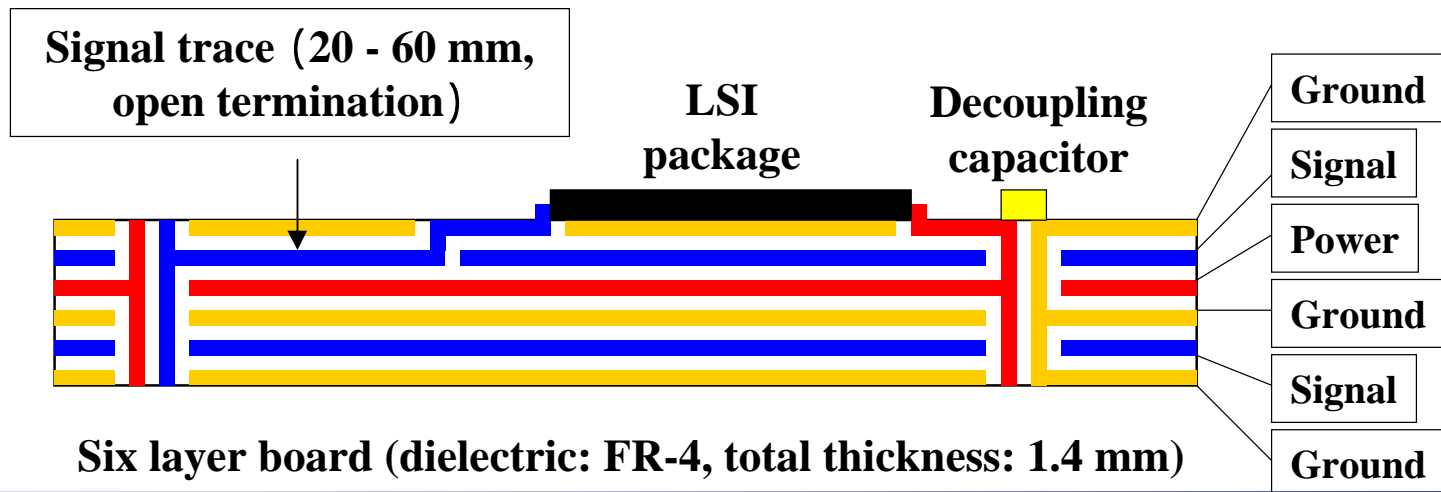
Electromagnetic near-field measurements over active devices

DUT for near- and far-fields evaluations

Width/interval
of pins
200 μm /500 μm



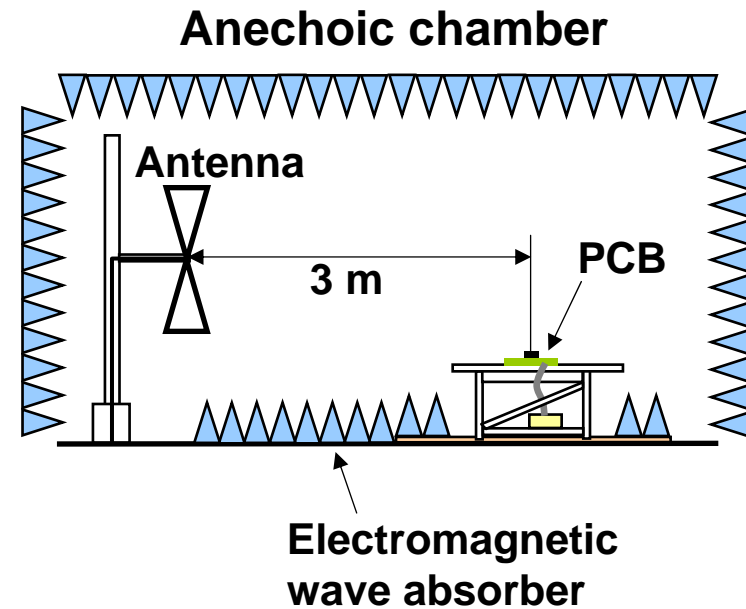
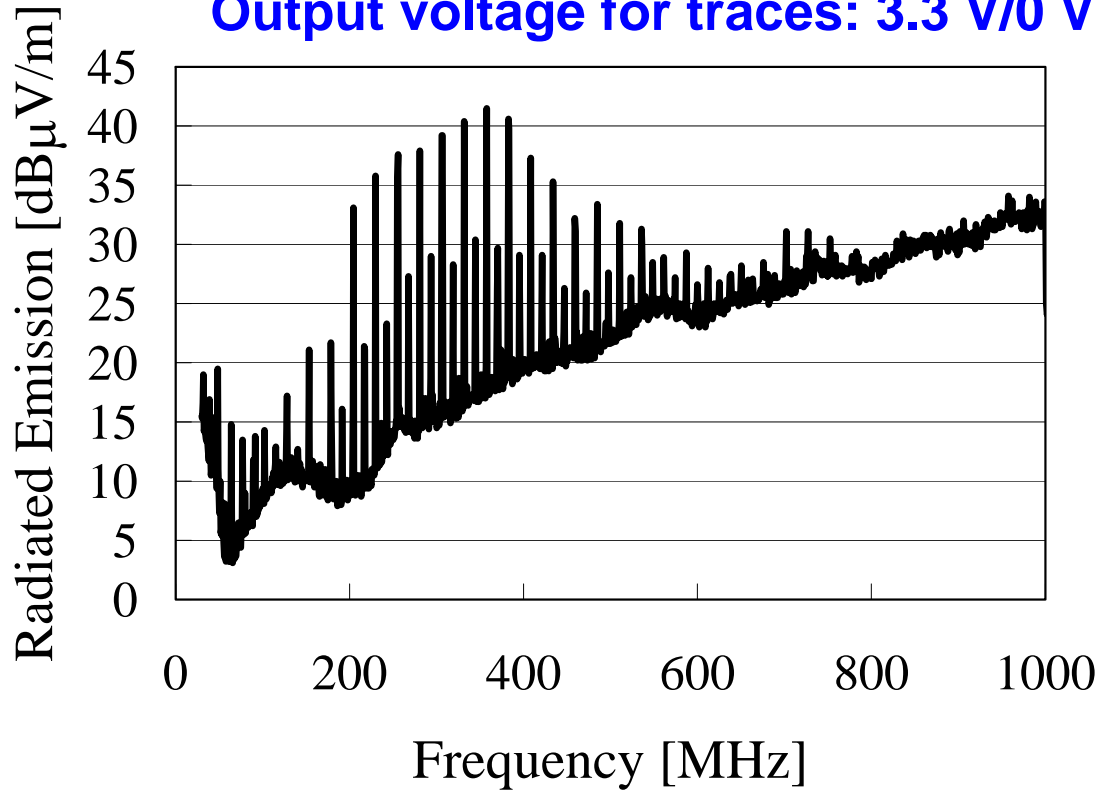
LSI Package (304 pin QFP)



Radiated electric field strength

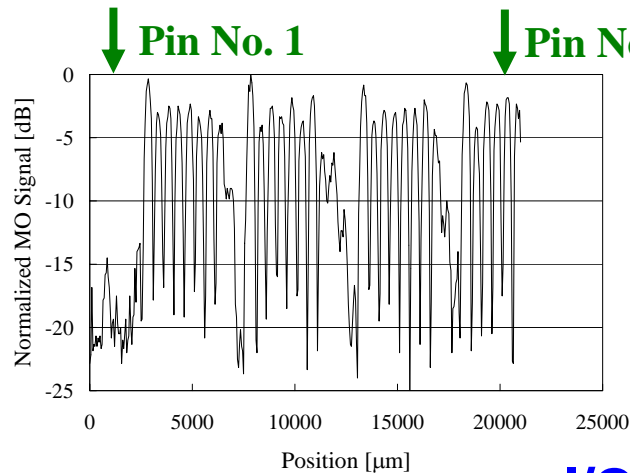
I/O circuit operation

Output voltage for traces: 3.3 V/0 V (rectangle, 12.75 MHz)



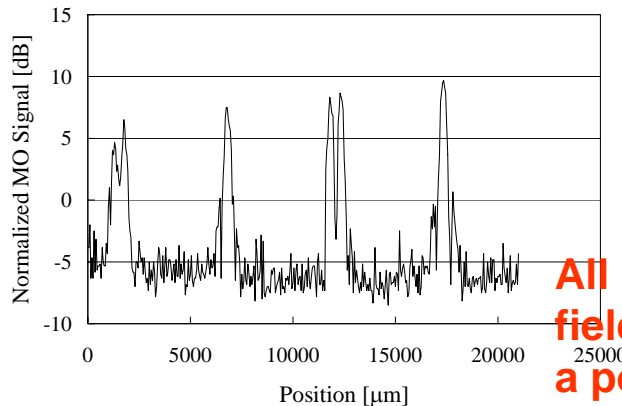
High-level emissions are observed at $12.75 \times 2n$ MHz.

Magnetic near-field distributions over the LSI package pins



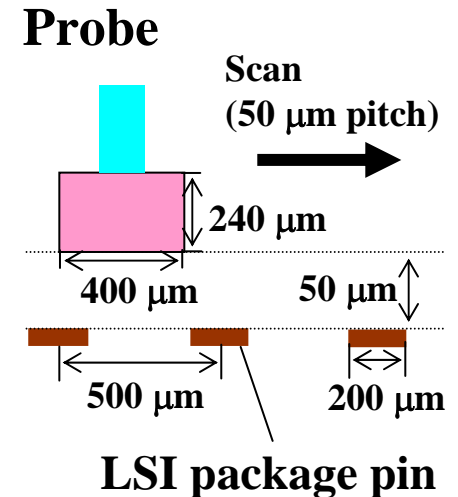
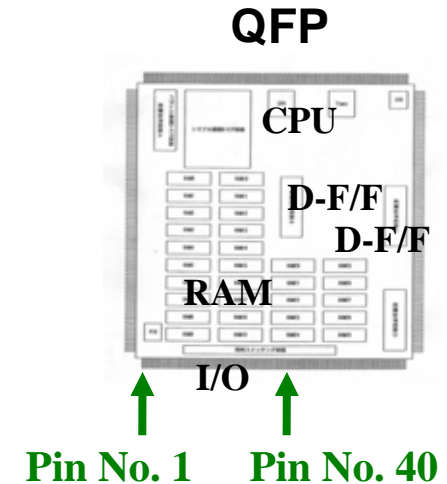
12.75 MHz

I/O circuit operation



127.5 MHz

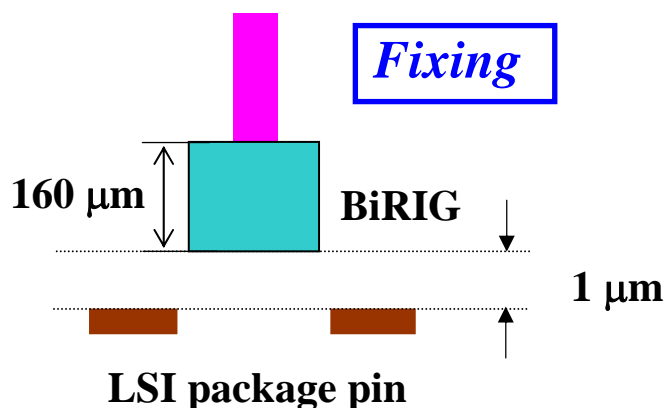
All peaks are due to the magnetic fields generating from the pins for a power or a ground



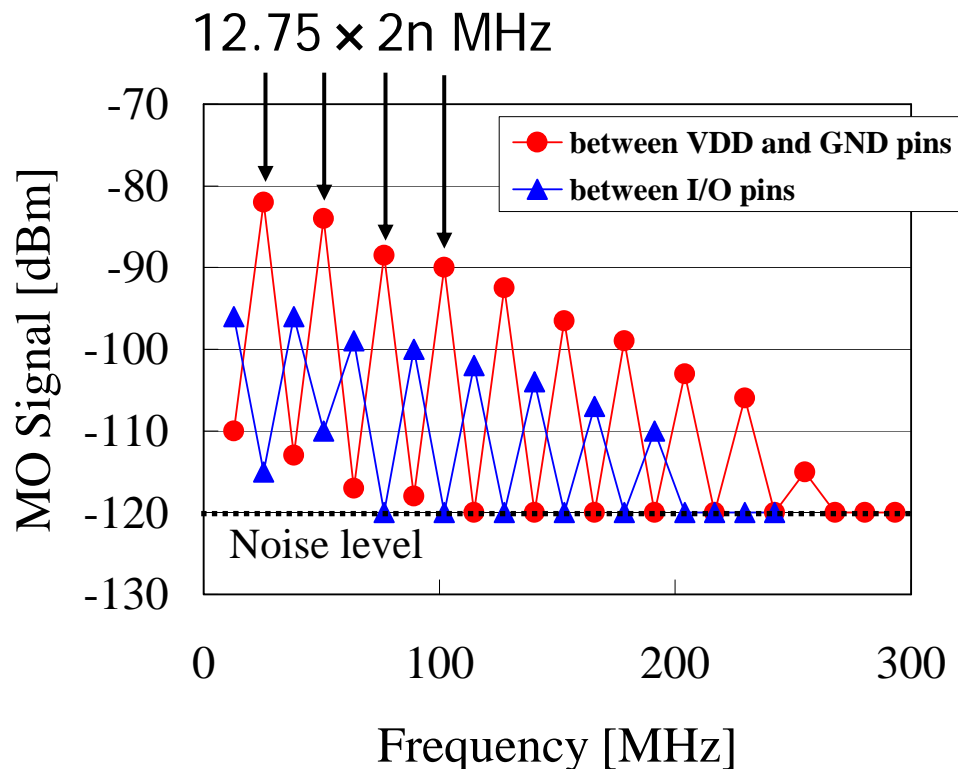
The probe has the capability for investigating circuit failure and an EMI source.

Frequency dependence of MO signals

Probe (Measurable bandwidth is over 10 GHz)



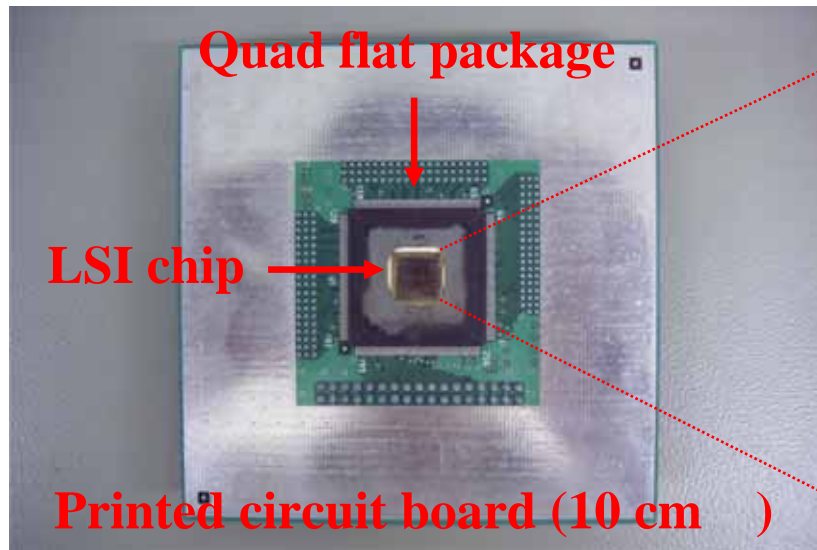
Measurement frequencies:
multiples of 12.75 MHz



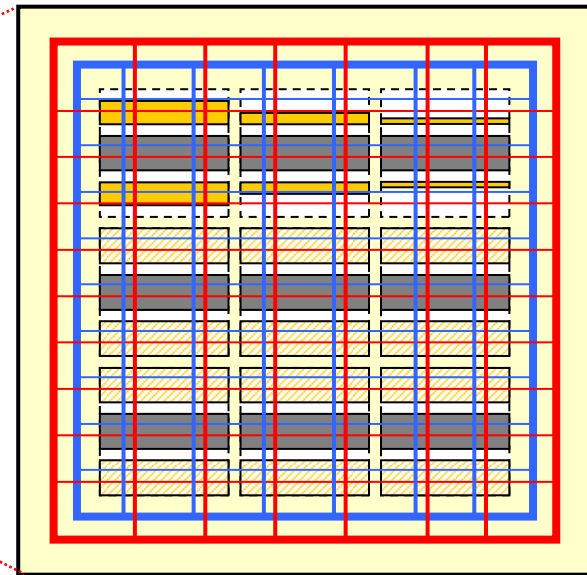
Between power and ground pins: high-level signals are observed at 12.75 x 2n MHz
(Same feature as the electric far-field characteristic)

This suggests that the origin of the high-level electric field radiation is a current flowing in the power supply system of the I/O circuits.

LSI chip for near-field measurements



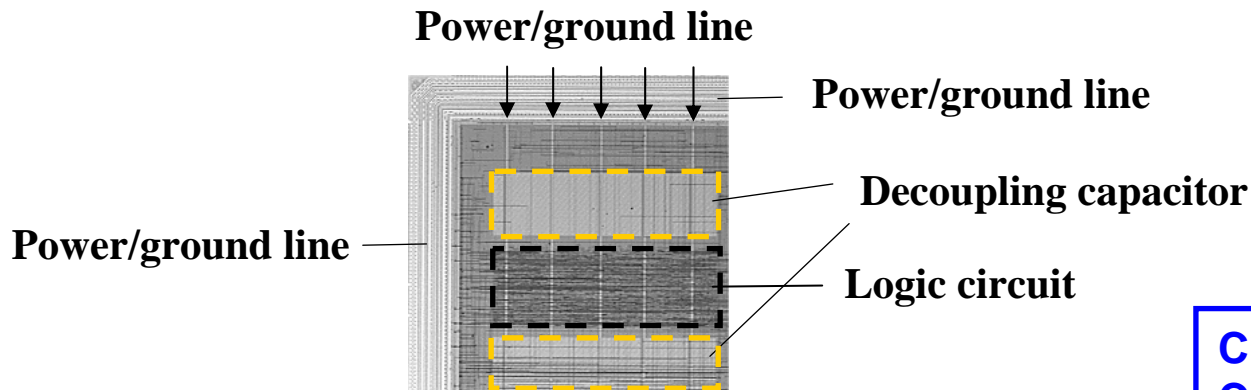
- Decoupling capacitor area
- Logic circuit area



10.4 mm

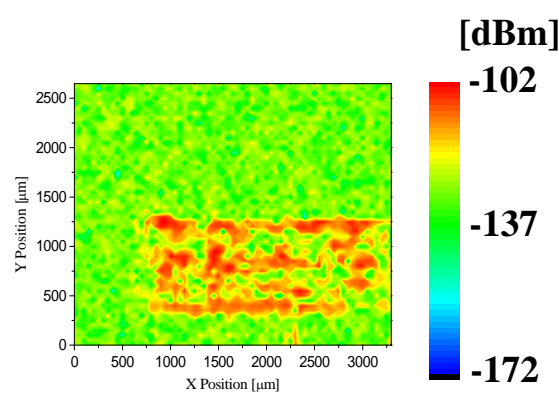
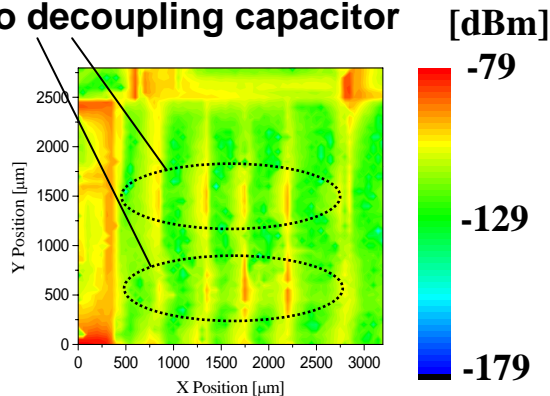
- Power/ground line for logic circuits
- Width of horizontal lines : $1.2 \mu\text{m}$
- Width of vertical lines : $10 \mu\text{m}$

Magnetic/electric near-field maps over an LSI chip



Clock frequency: 50MHz
Circuit operation frequency: 25 MHz
Measurement frequency: 50 MHz

Due to decoupling capacitor



Magnetic field distribution

Electric field distribution

Magnetic field: strong intensity above the power supply system

Electric field: strong intensity above the signal system

This suggests that detail SI/PI analyses can be performed by the EO/MO probing technique.

Conclusions

We introduced a wideband MO probe with a 10- μm -class spatial resolution.

GHz-region magnetic near-fields over a fine circuit were successfully mapped.

The potential of the probe for near-field characterization and EMI source evaluation of an active device was shown.

These results demonstrate that the FEMO/EO probing technique can be an effective tool toward an optimum design/packaging of electronic components.

Acknowledgement

This work was performed under the management of ASET in the basic plan of Research and Development on Ultra High-Density Electronics System Integration supported by NEDO.

This work was performed under the guidance and cooperation of Tsuchiya lab of the University of Tokyo.

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